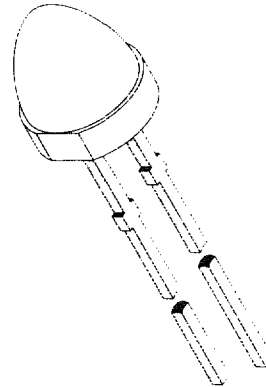


## Silicon NPN Phototransistor

### Description

S351P is a very high sensitive silicon NPN epitaxial planar phototransistor in a low profile  $\phi$  5mm (T-1 $\frac{3}{4}$ ) plastic package. Due to its waterclear epoxy the device is sensitive to visible and near infrared radiation.



94 S582

### Features

- Very high photo sensitivity (6mA)
- Low profile T-1 $\frac{3}{4}$  clear plastic package
- Angle of half sensitivity  $\phi = \pm 20^\circ$
- Suitable for visible and near IR radiation

### Applications

Optical switches  
Counters and sorters  
Interrupters  
Tape and card readers  
Encoders  
Position sensors

### Absolute Maximum Ratings

$T_{amb} = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
Collector Emitter Voltage		$V_{CEO}$	70	V
Emitter Collector Voltage		$V_{ECO}$	5	V
Collector Current		$I_C$	50	mA
Peak Collector Current	$t_p/T = 0.5$ , $t_p \leq 10$ ms	$I_{CM}$	100	mA
Total Power Dissipation	$T_{amb} \leq 25^\circ\text{C}$	$P_{tot}$	185	mW
Junction Temperature		$T_j$	100	$^\circ\text{C}$
Operating Temperature Range		$T_{amb}$	-55...+100	$^\circ\text{C}$
Storage Temperature Range		$T_{stg}$	-55...+100	$^\circ\text{C}$
Soldering Temperature	$t \leq 5$ s	$T_{sd}$	260	$^\circ\text{C}$
Thermal Resistance Junction/Ambient		$R_{thJA}$	400	K/W

## Basic Characteristics

$T_{amb} = 25^{\circ}\text{C}$

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Collector Emitter Breakdown Voltage	$I_C = 1\text{ mA}$	$V_{iBR/CEO}$	70			V
Collector Dark Current	$V_{CE} = 20\text{ V}, E = 0$	$I_{CEO}$		1	200	nA
Collector Emitter Capacitance	$V_{CE} = 5\text{ V}, f = 1\text{ MHz}, E=0$	$C_{CEO}$		6		pF
Collector Light Current	$E_c=1\text{ mW/cm}^2, \lambda=950\text{ nm}, V_{CE}=5\text{ V}$	$I_{ca}$	4	6		mA
Angle of Half Sensitivity		$\phi$		$\pm 20$		deg
Wavelength of Peak Sensitivity		$\lambda_p$		850		nm
Range of Spectral Bandwidth		$\lambda_{0.5}$		620...980		nm
Collector Emitter Saturation Voltage	$E_c=1\text{ mW/cm}^2, \lambda=950\text{ nm}, I_C=1\text{ mA}$	$V_{CEsat}$			0.3	V
Turn-On Time	$V_S=5\text{ V}, I_C=5\text{ mA}, R_L=100\Omega$	$t_{on}$		6		$\mu\text{s}$
Turn-Off Time	$V_S=5\text{ V}, I_C=5\text{ mA}, R_L=100\Omega$	$t_{off}$		5		$\mu\text{s}$
Cut-Off Frequency	$V_S=5\text{ V}, I_C=5\text{ mA}, R_L=100\Omega$	$f_c$		110		kHz

## Typical Characteristics ( $T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified)

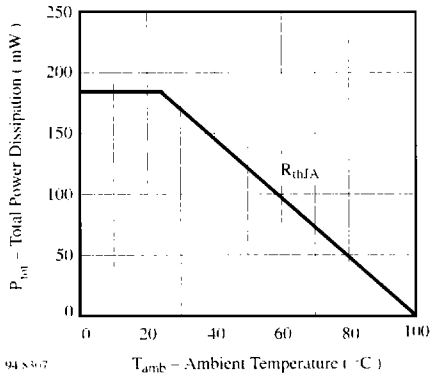


Figure 1. Total Power Dissipation vs. Ambient Temperature

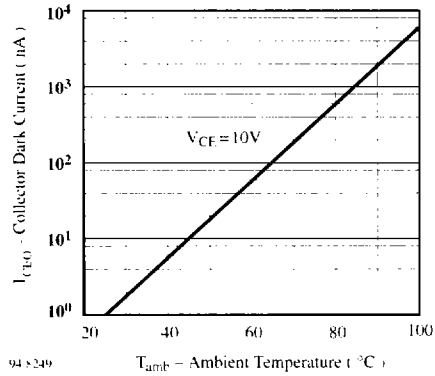


Figure 2. Collector Dark Current vs. Ambient Temperature

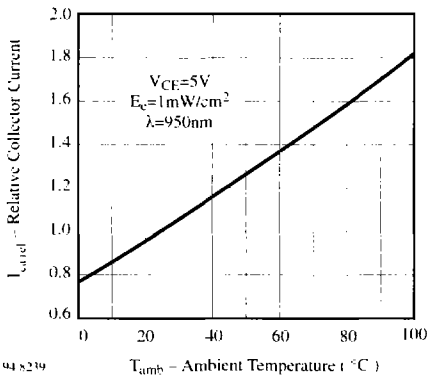


Figure 3. Relative Collector Current vs. Ambient Temperature

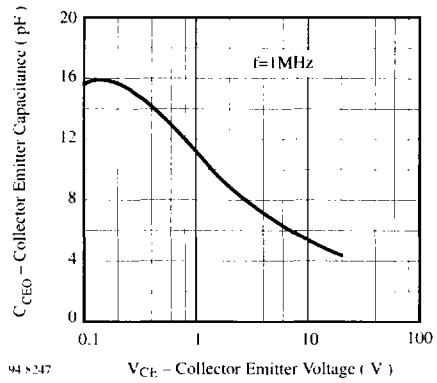


Figure 6. Collector Emitter Capacitance vs. Collector Emitter Voltage

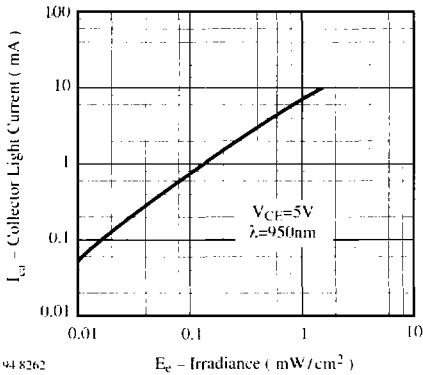


Figure 4. Collector Light Current vs. Irradiance

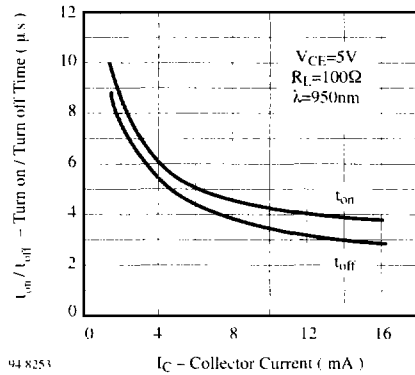


Figure 7. Turn On/Turn Off Time vs. Collector Current

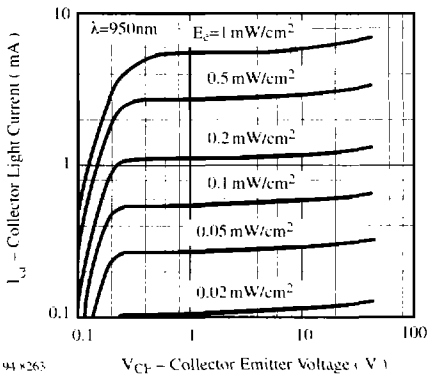


Figure 5. Collector Light Current vs. Collector Emitter Voltage

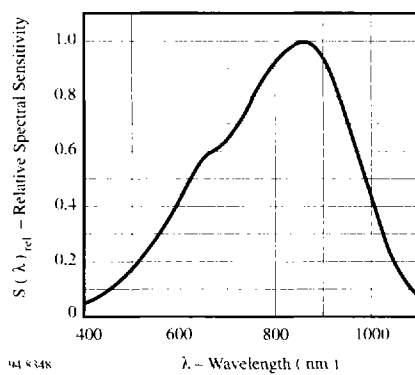
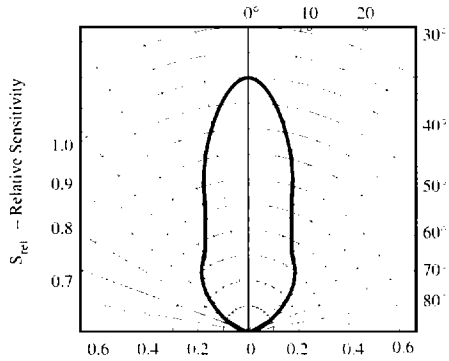


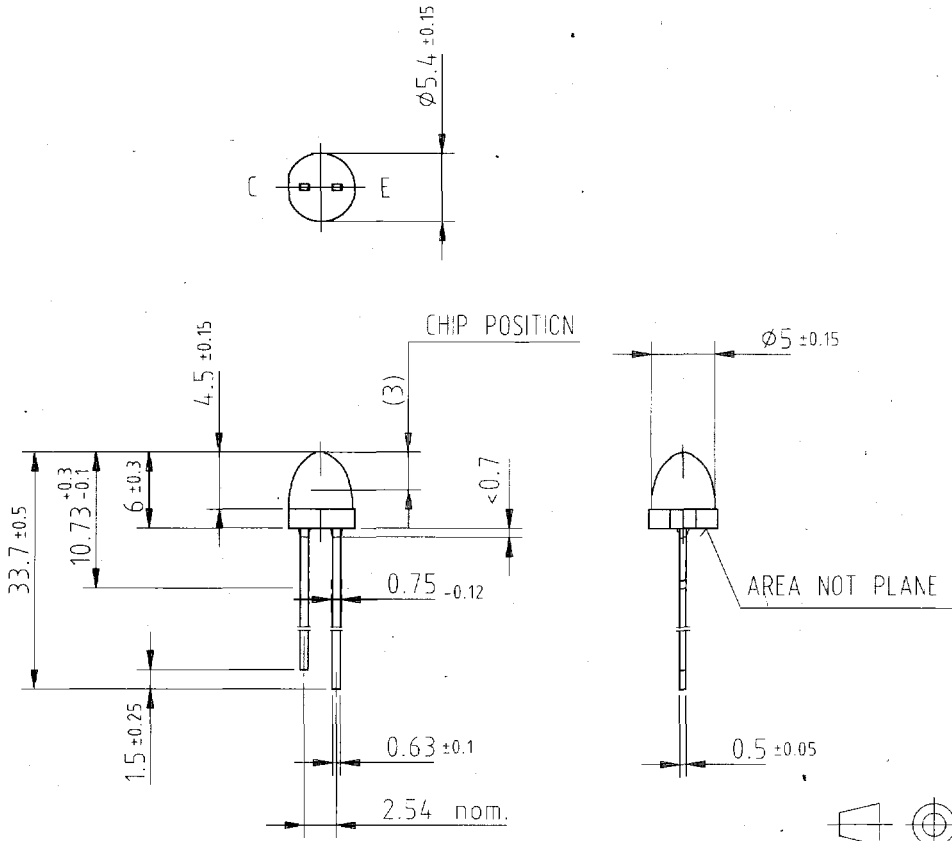
Figure 8. Relative Spectral Sensitivity vs. Wavelength



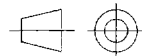
94 x 264

Figure 9. Relative Radiant Sensitivity vs. Angular Displacement

**Dimensions in mm**



9612204



technical drawings  
according to DIN  
specifications